

# SiC

Silicon Carbide Diode

## 2nd Generation thinQ!™

2nd Generation thinQ!™ SiC Schottky Diode  
IDV02S60C

## Data Sheet

Rev. 2.0, 2010-05-31  
Final

Industrial & Multimarket

## 2nd Generation thinQ!™ SiC Schottky Diode

IDV02S60C

### 1 Description

The second generation of Infineon SiC Schottky diodes has emerged over the years as the industry standard. The IDVxxS60C family is extending the already broad portfolio with the TO220FullPAK package. In order to greatly reduce the impact of the internal isolation of the FullPAK on the thermal performance, Infineon is applying its patented diffusion soldering process for attaching the chip to the leadframe. The result is nearly identical thermal characteristics to those of the SiC diodes in the non-isolated TO220 package.



#### Features

- Revolutionary semiconductor material - Silicon Carbide
- Nearly no reverse / forward recovery charge
- High surge current capability
- Fully isolated package with nearly similar  $R_{th,jc}$  as the standard T0220
- Suitable for high temperature operation
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Switching behavior independent of forward current, switching speed and temperature

#### Benefits

- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Good thermal performance without the need for additional isolation layer and washer
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures and less fans
- Reduced EMI



#### Applications

Fully isolated TO220 package for e.g. CCM PFC; Motor Drives; Solar Applications; UPS

**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DC}$	600	V
$Q_C$	3.2	nC
$I_F @ T_C < 120^\circ\text{C}$	2	A

**Table 2 Pin Definition**

Pin 1	Pin2	Pin 3
C	A	n.a.

Type / Ordering Code	Package	Marking	Related Links
IDV02S60C	PG-TO220 FullPAK	D02S60C	<a href="#">IFX SiC Diodes Webpage</a>

1) J-STD20 and JESD22

## Table of Contents

1	Description .....	2
	Table of Contents .....	3
2	Maximum ratings .....	4
3	Thermal characteristics .....	4
4	Electrical characteristics .....	5
5	Electrical characteristics diagrams .....	6
6	Package outlines .....	9
7	Revision History .....	10

## 2 Maximum ratings

Table 3 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous forward current	$I_F$	-	-	2	A	$T_C = < 120^\circ\text{C}$
Surge non-repetitive forward current, sine halfwave	$I_{F, SM}$	-	-	11.5		$T_C = 25^\circ\text{C}, t_p = 10 \text{ ms}$
		-	-	9.7		$T_C = 150^\circ\text{C}, t_p = 10 \text{ ms}$
Non-repetitive peak forward current	$I_{F, max}$	-	-	100		$T_C = 25^\circ\text{C}, t_p = 10 \mu\text{s}$
$i^2 t$ value	$\int i^2 dt$	-	-	0.61	A <sup>2</sup> s	$T_C = 25^\circ\text{C}, t_p = 10 \text{ ms}$
		-	-	0.44		$T_C = 150^\circ\text{C}, t_p = 10 \text{ ms}$
Repetitive peak reverse voltage	$V_{RRM}$	-	-	600	V	$T_j = 25^\circ\text{C}$
Diode dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_R = 0 \dots 480 \text{ V}$
Power dissipation	$P_{tot}$	-	-	18	W	$T_C = 25^\circ\text{C}$
Operating and storage temperature	$T_j, T_{stg}$	- 55	-	175	°C	
Mounting torque		-	-	50	Ncm	M2.5 screws

## 3 Thermal characteristics

Table 4 Thermal characteristics TO-220 FullPAK

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	8.5	K/W	
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62		leaded
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

## 4 Electrical characteristics

**Table 5 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
DC blocking voltage	$V_{DC}$	600	-	-	V	$T_j = 25\text{ °C}$ , $I_R = 0.015\text{ mA}$
Diode forward voltage	$V_F$	-	1.7	1.9		$I_F = 2\text{ A}$ , $T_j = 25\text{ °C}$
		-	2.1	2.6		$I_F = 2\text{ A}$ , $T_j = 150\text{ °C}$
Reverse current	$I_R$	-	0.23	15	$\mu\text{A}$	$I_R = 600\text{ V}$ , $T_j = 25\text{ °C}$
		-	1	150		$I_R = 600\text{ V}$ , $T_j = 150\text{ °C}$

**Table 6 AC characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Total capacitive charge	$Q_c$	-	3.2	-	nC	$V_R = 400\text{ V}$ , $F \leq F_{max}$
Switching time <sup>1)</sup>	$t_c$	-	-	<10	ns	$di_F/dt = 200\text{ A}/\mu\text{s}$ , $T_j = 150\text{ °C}$
		$C$	-	60		
	-		8	-	$V_R = 300\text{ V}$ , $f = 1\text{ MHz}$	
	-		8	-	$V_R = 600\text{ V}$ , $f = 1\text{ MHz}$	

<sup>1)</sup>  $t_c$  is the time constant for the capacitive displacement current waveform (independent from  $T_j$ ,  $I_{LOAD}$  and  $di/dt$ ), different from  $t_{rr}$  which is dependent on  $T_j$ ,  $I_{LOAD}$  and  $di/dt$ . No reverse recovery time constant  $t_{rr}$  due to absence of minority carrier injection.

5 Electrical characteristics diagrams

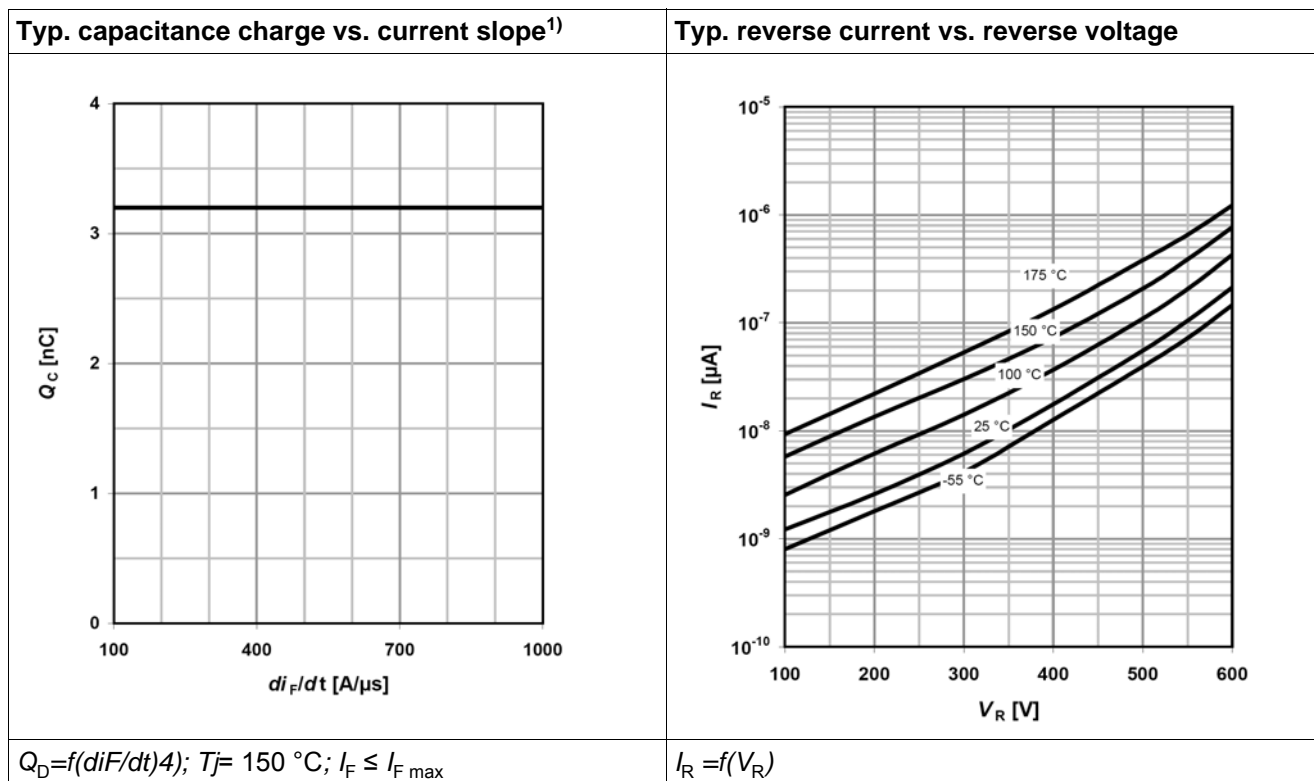
Table 7

Power dissipation	Diode forward current
$P_{tot} = f(T_C)$	$I_F = f(T_C); T_j \leq 175 \text{ } ^\circ\text{C}$

Table 8

Typ. forward characteristic	Typ. forward characteristic in surge current
$I_F = f(V_F); t_p = 400 \text{ } \mu\text{s}; \text{ parameter: } T_j$	$I_F = f(V_F); t_p = 400 \text{ } \mu\text{s}; \text{ parameter: } T_j$

Table 9



1) Only capacitive charge occurring, guaranteed by design

Table 10

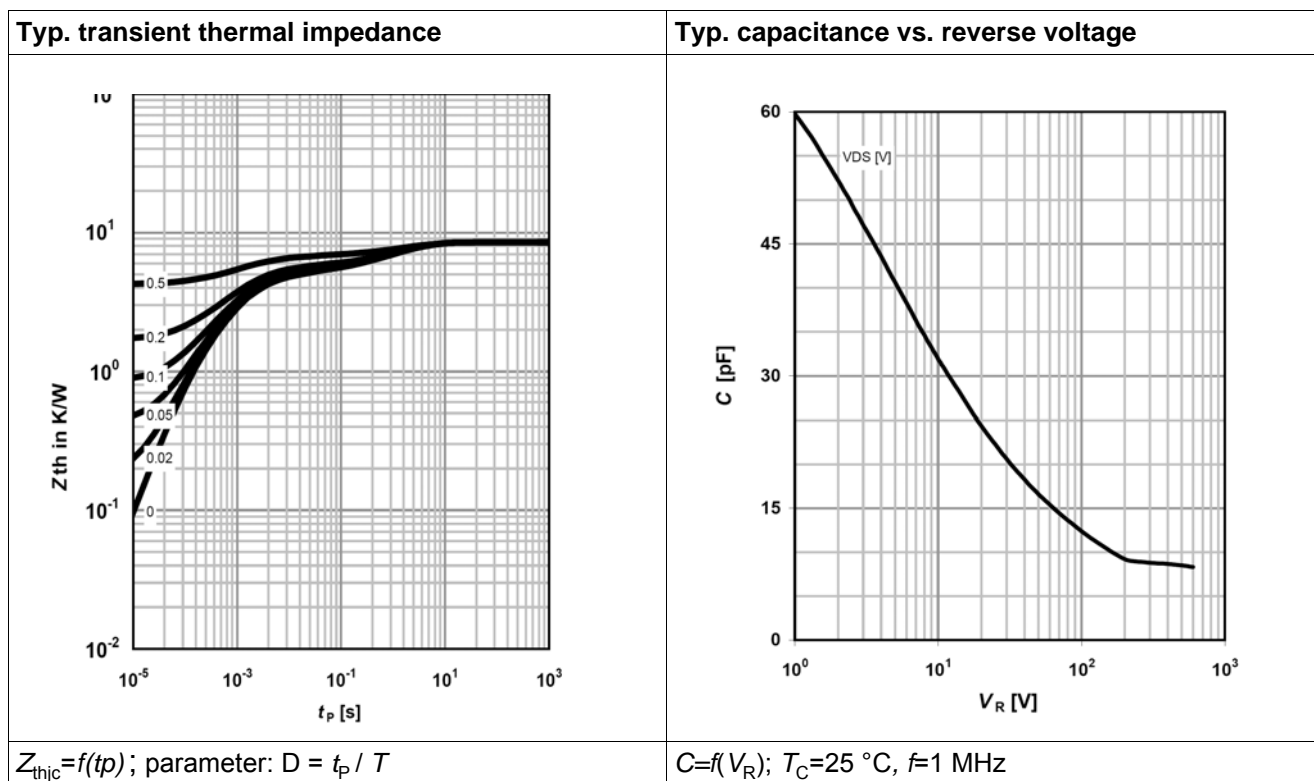
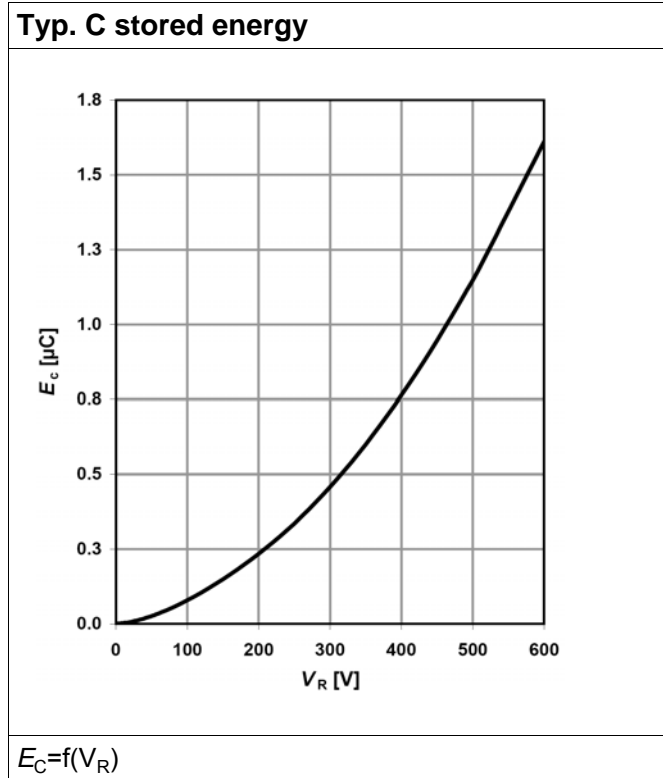


Table 11





6 Package outlines

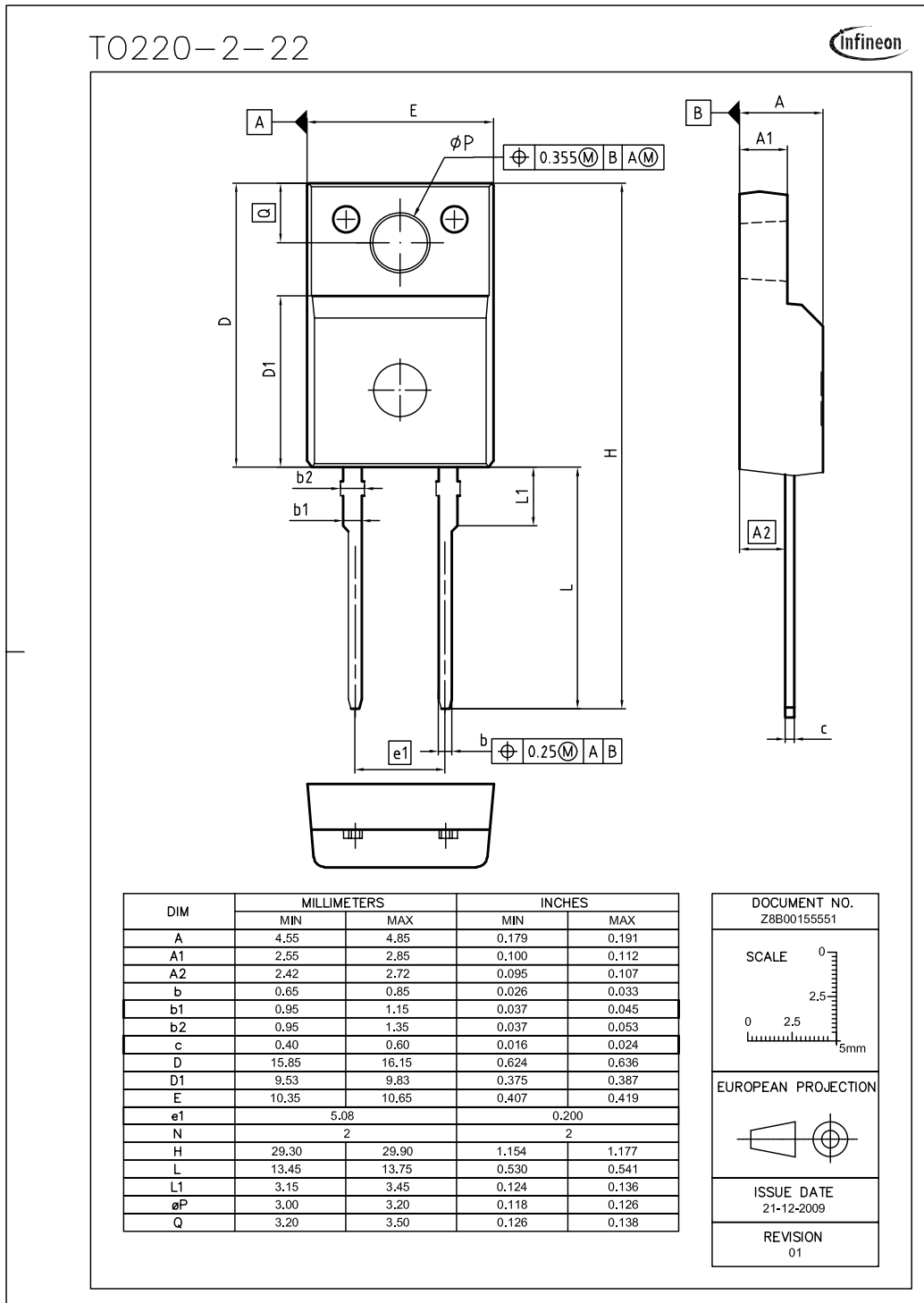


Figure 1 Outlines TO-220 FullPAK, dimensions in mm/inches

## 7 Revision History

### 2nd Generation thinQ!™ 2nd Generation thinQ!™ SiC Schottky Diode

Revision History: 2010-05-31, Rev. 2.0

#### Previous Revision:

Revision	Subjects (major changes since last revision)
2.0	Release of final data sheet

#### We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all?  
Your feedback will help us to continuously improve the quality of this document.

Please send your proposal (including a reference to this document) to: [erratum@infineon.com](mailto:erratum@infineon.com)



Edition 2010-05-31

Published by  
Infineon Technologies AG  
81726 Munich, Germany

© 2010 Infineon Technologies AG  
All Rights Reserved.

#### Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

#### Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

#### Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.